



# FDMC8882

## N-Channel Power Trench<sup>®</sup> MOSFET

30 V, 16 A, 14.3 mΩ

### Features

- Max  $r_{DS(on)}$  = 14.3 mΩ at  $V_{GS} = 10\text{ V}$ ,  $I_D = 10.5\text{ A}$
- Max  $r_{DS(on)}$  = 22.5 mΩ at  $V_{GS} = 4.5\text{ V}$ ,  $I_D = 8.3\text{ A}$
- High performance technology for extremely low  $r_{DS(on)}$
- Termination is Lead-free and RoHS Compliant

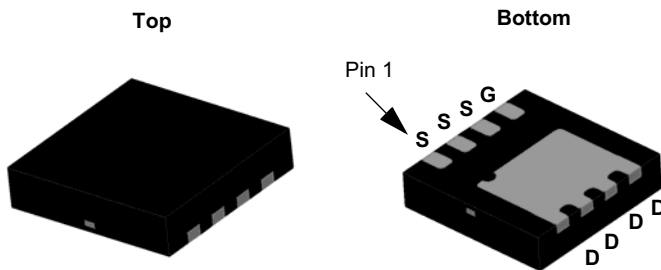


### General Description

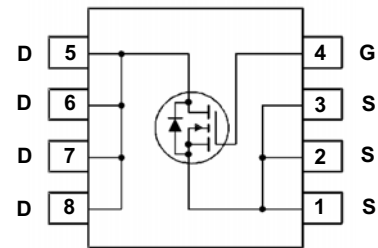
This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced Power Trench<sup>®</sup> process that has been especially tailored to minimize the on-state resistance. This device is well suited for Power Management and load switching applications common in Notebook Computers and Portable Battery Packs.

### Application

- High side in DC - DC Buck Converters
- Notebook battery power management
- Load switch in Notebook



MLP 3.3x3.3



### MOSFET Maximum Ratings $T_A = 25\text{ °C}$ unless otherwise noted

Symbol	Parameter	Rated	Units
$V_{DS}$	Drain to Source Voltage	30	V
$V_{GS}$	Gate to Source Voltage	$\pm 20$	V
$I_D$	Drain Current -Continuous (Package limited) $T_C = 25\text{ °C}$	16	A
	-Continuous (Silicon limited) $T_C = 25\text{ °C}$	34	
	-Continuous $T_A = 25\text{ °C}$ (Note 1a)	10.5	
	-Pulsed	40	
$P_D$	Power Dissipation $T_C = 25\text{ °C}$	18	W
	Power Dissipation $T_A = 25\text{ °C}$ (Note 1a)	2.3	
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150	$^{\circ}\text{C}$

### Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	6.6	$^{\circ}\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	53	

### Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMC8882	FDMC8882	MLP 3.3x3.3	13 "	12 mm	3000 units

## Electrical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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### Off Characteristics

$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 250\text{ }\mu\text{A}$ , $V_{GS} = 0\text{ V}$	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$ , referenced to $25\text{ }^\circ\text{C}$		25		mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 24\text{ V}$ , $V_{GS} = 0\text{ V}$ $T_J = 125\text{ }^\circ\text{C}$			1 250	$\mu\text{A}$
$I_{GSS}$	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{ V}$ , $V_{DS} = 0\text{ V}$			$\pm 100$	nA

### On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = 250\text{ }\mu\text{A}$	1.2	1.9	2.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$ , referenced to $25\text{ }^\circ\text{C}$		-5		mV/ $^\circ\text{C}$
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{ V}$ , $I_D = 10.5\text{ A}$		12.4	14.3	m $\Omega$
		$V_{GS} = 4.5\text{ V}$ , $I_D = 8.3\text{ A}$		16.0	22.5	
		$V_{GS} = 10\text{ V}$ , $I_D = 10.5\text{ A}$ $T_J = 125\text{ }^\circ\text{C}$		17.4		
$g_{FS}$	Forward Transconductance	$V_{DD} = 5\text{ V}$ , $I_D = 10.5\text{ A}$		33		S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = 15\text{ V}$ , $V_{GS} = 0\text{ V}$ , $f = 1\text{ MHz}$		710	945	pF
$C_{oss}$	Output Capacitance			140	185	pF
$C_{rss}$	Reverse Transfer Capacitance			90	135	pF
$R_g$	Gate Resistance			1.0		$\Omega$

### Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 15\text{ V}$ , $I_D = 10.5\text{ A}$ , $V_{GS} = 10\text{ V}$ , $R_{GEN} = 6\text{ }\Omega$		7	14	ns
$t_r$	Rise Time			3	10	ns
$t_{d(off)}$	Turn-Off Delay Time			17	30	ns
$t_f$	Fall Time			2	10	ns
$Q_{g(TOT)}$	Total Gate Charge		$V_{GS} = 0\text{ V to } 10\text{ V}$		14	20
	Total Gate Charge	$V_{GS} = 0\text{ V to } 4.5\text{ V}$	$V_{DD} = 15\text{ V}$ $I_D = 10.5\text{ A}$	7	10	nC
$Q_{gs}$	Total Gate Charge			2.3		nC
$Q_{gd}$	Gate to Drain "Miller" Charge			2.8		nC

### Drain-Source Diode Characteristics

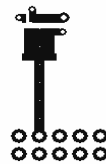
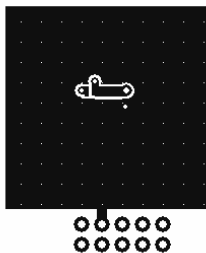
$V_{SD}$	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{ V}$ , $I_S = 10.5\text{ A}$ (Note 2)		0.88	1.2	V
		$V_{GS} = 0\text{ V}$ , $I_S = 1.9\text{ A}$ (Note 2)		0.76	1.2	
$t_{rr}$	Reverse Recovery Time	$I_F = 10.5\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$		16	28	ns
$Q_{rr}$	Reverse Recovery Charge			4.4	10	nC

#### NOTES:

1.  $R_{\theta JA}$  is determined with the device mounted on a  $1\text{ in}^2$  pad 2 oz copper pad on a  $1.5 \times 1.5\text{ in.}$  board of FR-4 material.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.

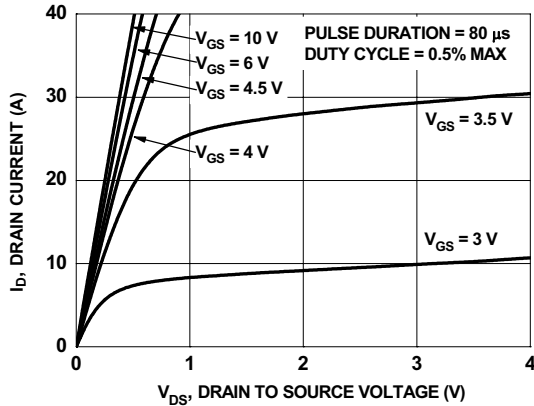
a.  $53\text{ }^\circ\text{C/W}$  when mounted on  
a  $1\text{ in}^2$  pad of 2 oz copper

b.  $125\text{ }^\circ\text{C/W}$  when mounted on  
a minimum pad of 2 oz copper

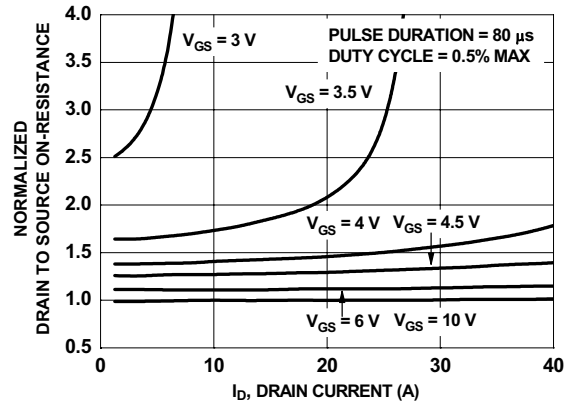


2. Pulse Test: Pulse Width <  $300\text{ }\mu\text{s}$ , Duty cycle <  $2.0\%$ .

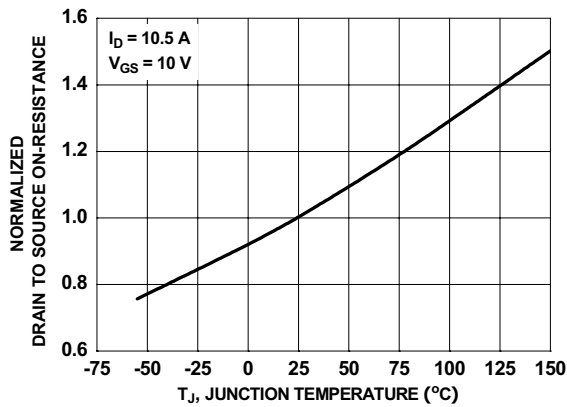
**Typical Characteristics**  $T_J = 25\text{ }^\circ\text{C}$  unless otherwise noted



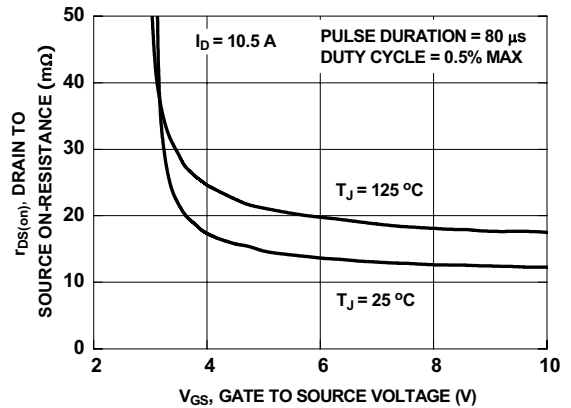
**Figure 1. On-Region Characteristics**



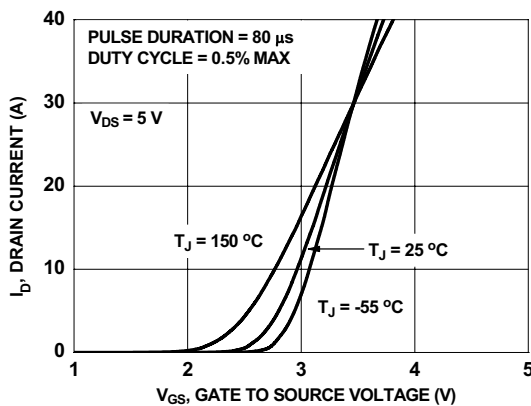
**Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage**



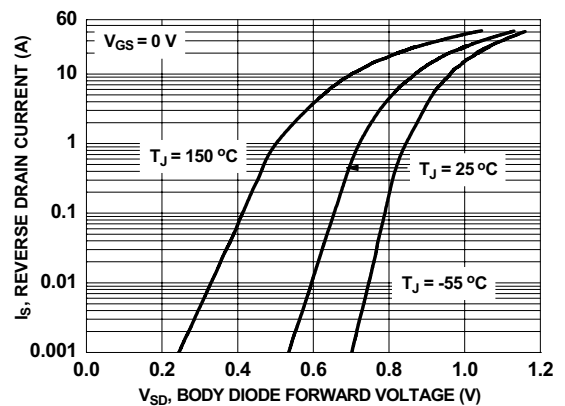
**Figure 3. Normalized On-Resistance vs Junction Temperature**



**Figure 4. On-Resistance vs Gate to Source Voltage**

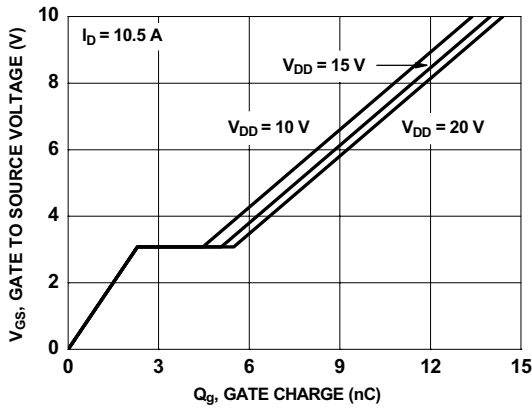


**Figure 5. Transfer Characteristics**

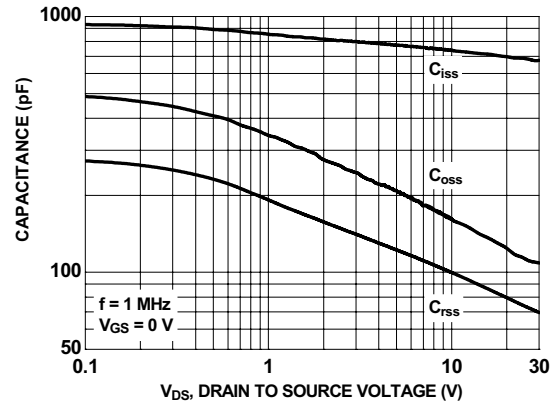


**Figure 6. Source to Drain Diode Forward Voltage vs Source Current**

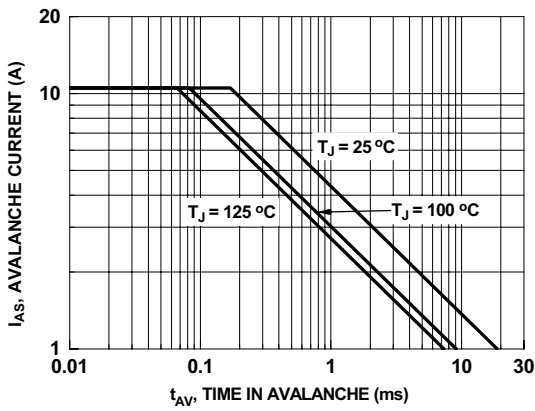
**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted



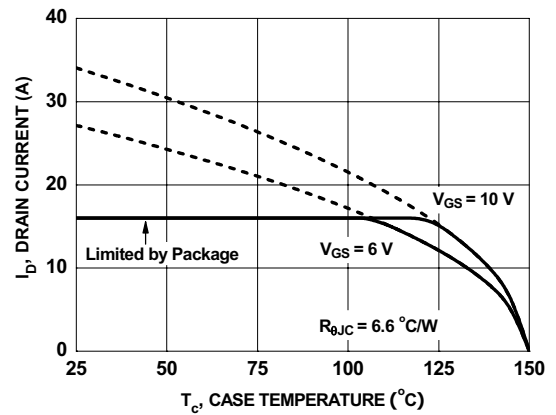
**Figure 7. Gate Charge Characteristics**



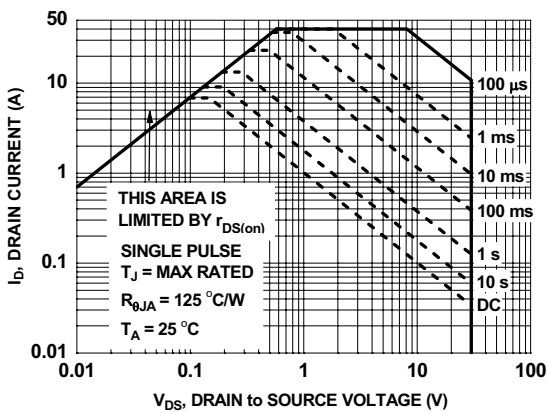
**Figure 8. Capacitance vs Drain to Source Voltage**



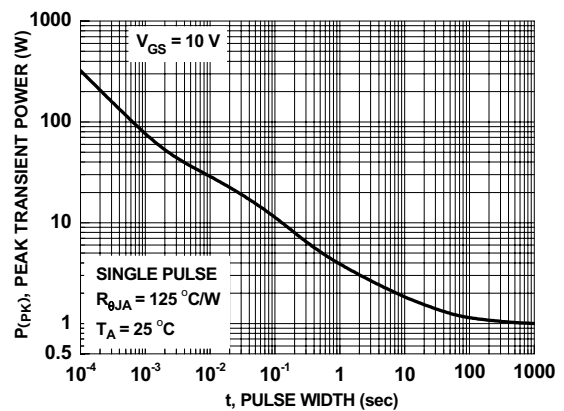
**Figure 9. Unclamped Inductive Switching Capability**



**Figure 10. Maximum Continuous Drain Current vs Case Temperature**

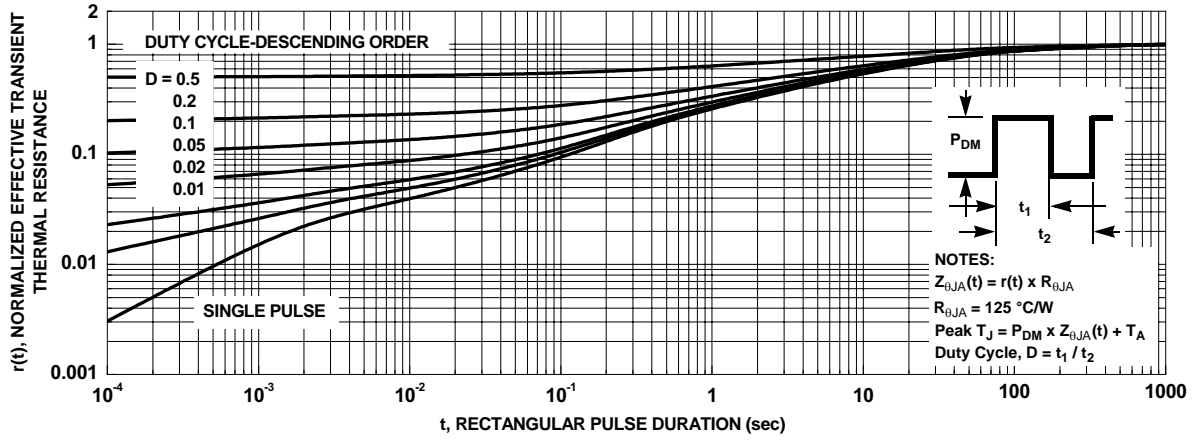


**Figure 11. Forward Bias Safe Operating Area**

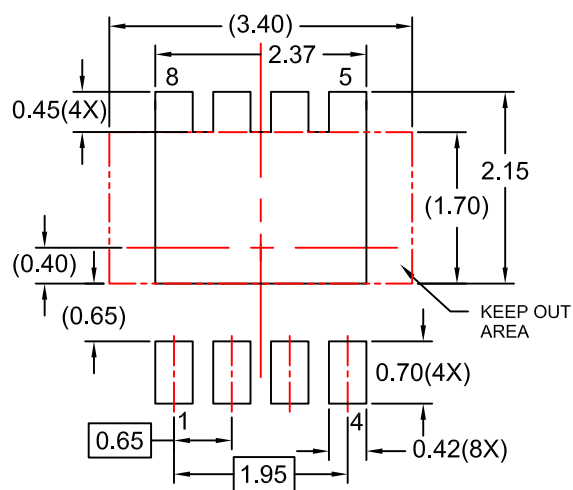
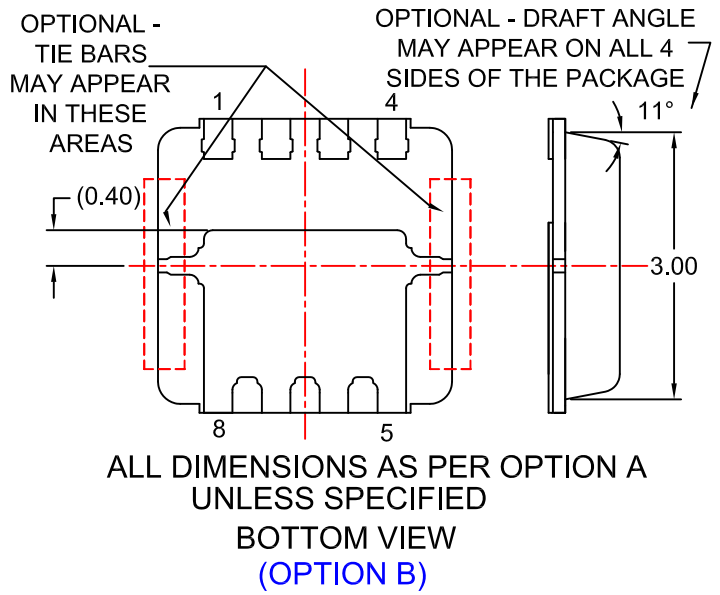
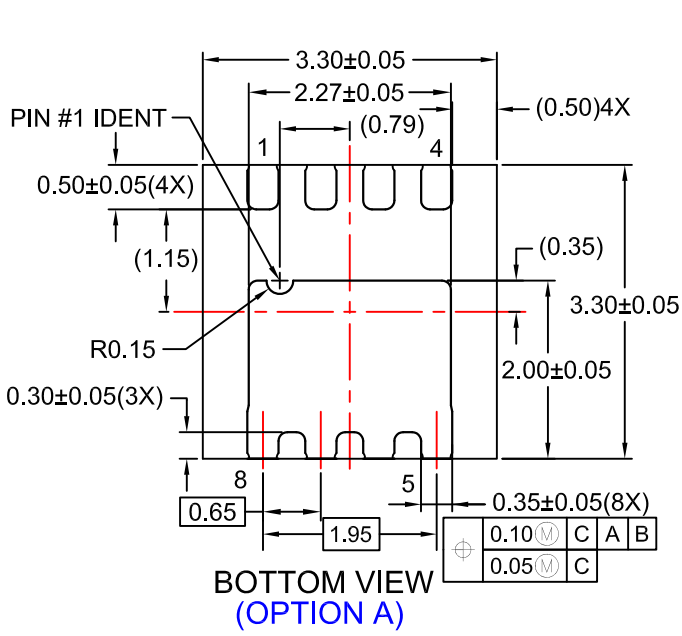
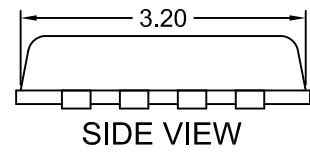
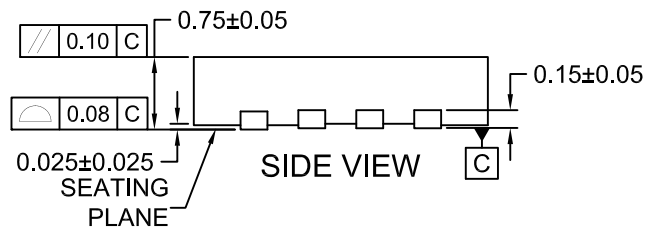
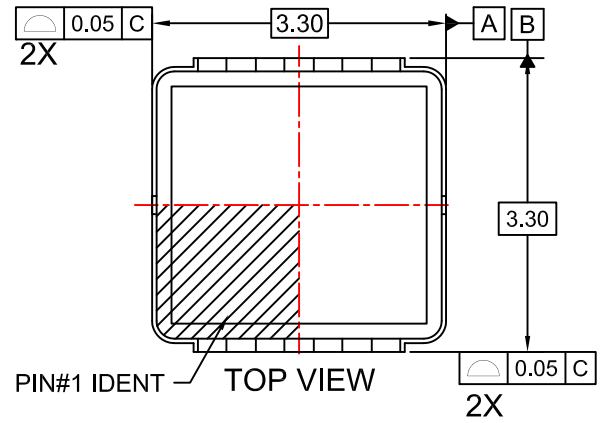
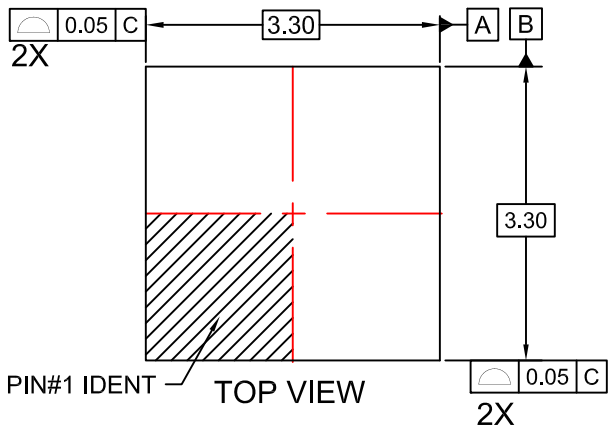


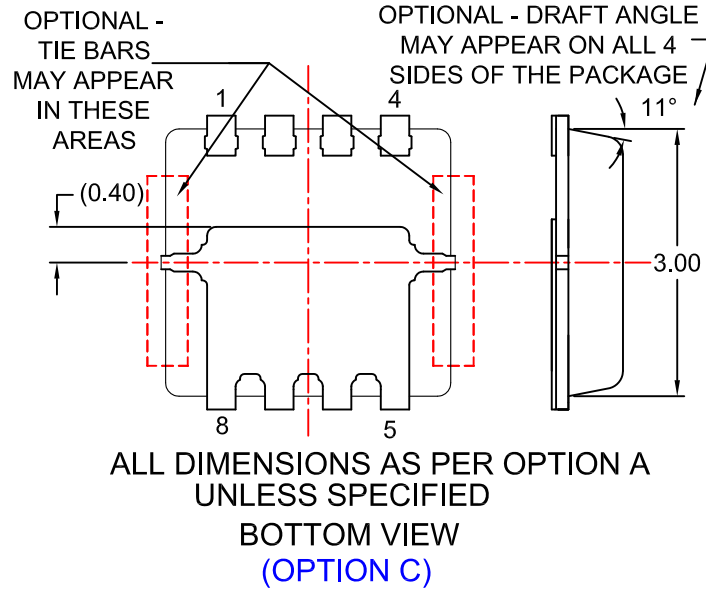
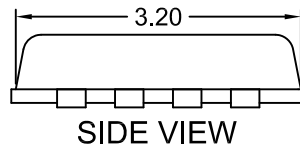
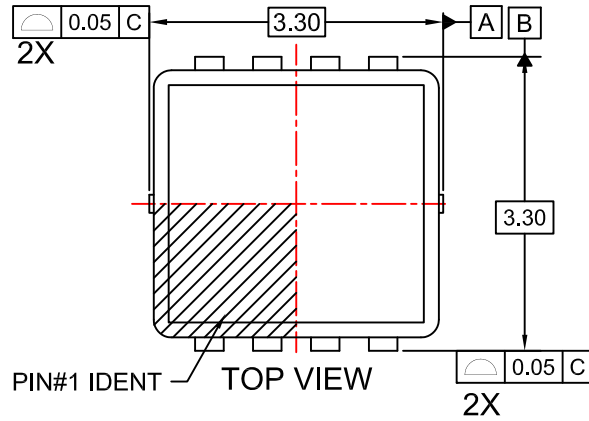
**Figure 12. Single Pulse Maximum Power Dissipation**

**Typical Characteristics**  $T_J = 25\text{ }^\circ\text{C}$  unless otherwise noted



**Figure 13. Transient Thermal Response Curve**





**NOTES:**

- A. PACKAGE DOES NOT FULLY CONFORM TO JEDEC REGISTRATION MO-240.
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.
- D. LAND PATTERN RECOMMENDATION IS EXISTING INDUSTRY LAND PATTERN
- E. DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. BURRS OR MOLD FLASH SHALL NOT EXCEED 0.10MM.
- F. DRAWING FILENAME: MKT-MLP08Wrev3.
- G. OPTION A - SAWN MLP, OPTIONS B & C - PUNCH MLP.



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